

MOS FIELD EFFECT TRANSISTOR

DESCRIPTION:

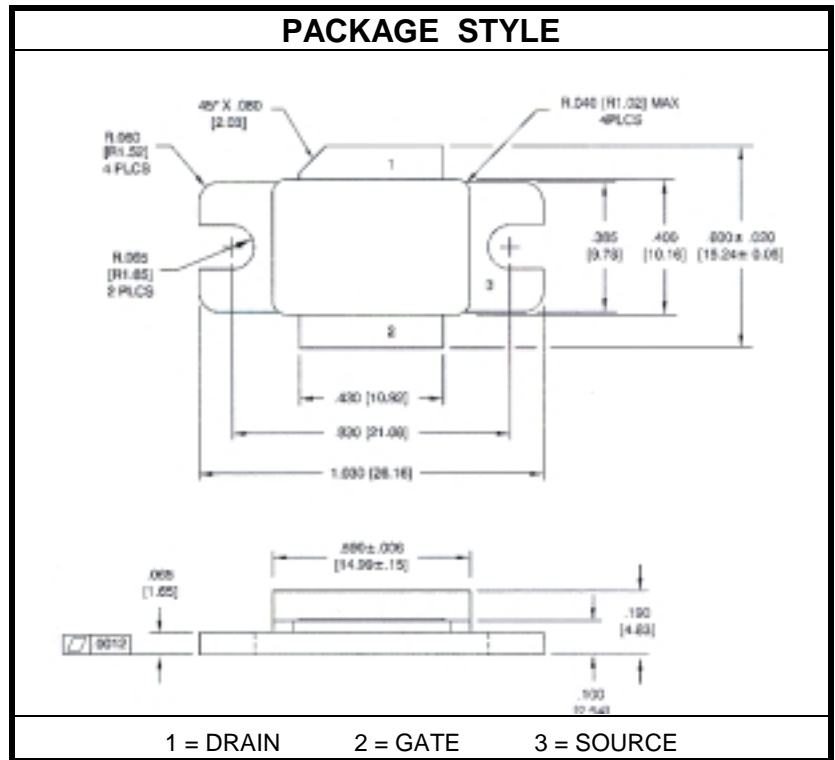
The **ASI PTF10019** is Designed for Cellular, GSM, and D-AMPS applications from 860 tp 960 MHz.

FEATURES:

- 70 W, 860-960 MHz
- Internally matched
- **Omnigold™** Metalization System
- Silicon Nitride Passivated

MAXIMUM RATINGS

V_{DSS}	65 V
V_{GS}	± 20 V
P_{DISS}	215 W @ $T_C = 25^\circ C$
T_J	-40 °C to +200 °C
T_{STG}	-40 °C to +150 °C
θ_{JC}	0.8 °C/W


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	$V_{GS} = 0$ V	$I_D = 25$ mA		65			V
I_{DSS}	$V_{DS} = 26$ V					1.0	mA
$V_{GS(th)}$	$V_{DS} = 10$ V	$I_D = 75$ mA		3.0		5.0	V
G_{fs}	$V_{DS} = 10$ V	$I_D = 3.0$ A			3.0		Siemens
P_G	$V_{DD} = 28$ V $f = 960$ MHz	$P_{OUT} = 70$ W	$I_{DQ} = 600$ mA	13.0	14.5		dB
η_c				45	50		%
P-1dB				70	75		W
Ψ							10:1